RJE0605JPV

Silicon P Channel MOS FET Series
Power Switching

R07DS1393EJ0100
Rev.1.00
Apr.07.2025

Description

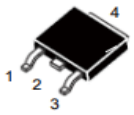
This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc..

Functions

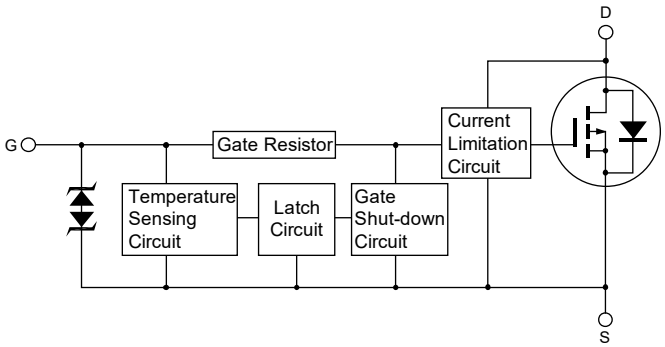
- Logic level operation (-6 V Gate drive)
- High endurance capability against to the short circuit
- Built-in the over temperature shut-down circuit
- Latch type shut down operation (need 0 voltage recovery)
- Built-in the current limitation circuit
- Low on-resistance RDS(on) : 58 mΩ Typ, 75 mΩ Max (V_{GS} = –10 V)
- AEC-Q101 Compliant

Outline

RENESAS Package code: PRSS0004ZV-A
(Package name: MP-3ZK)



1. Gate
2. Drain
3. Source
4. Fin (Drain)



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	–60	V
Gate to source voltage	V_{GSS}	–16	V
Gate to source voltage	V_{GSS}	2.5	V
Drain current	I_D Note 3	–10	A
Body-drain diode reverse drain current	I_{DR}	–10	A
Avalanche current	I_{AP} Notes 2	–7	A
Avalanche energy	E_{AR} Notes 2	210	mJ
Channel dissipation	Pch Notes 1	30	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. Tc = 25 °C
2. Tch = 25 °C, Rg ≥ 50 Ω
3. It provides by the current limitation lower bound value.

Typical Operation Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input voltage	V_{IH}	–3.5	—	—	V	
	V_{IL}	—	—	–1.2	V	
Input current (Gate non shut down)	I_{IH1}	—	—	–100	μA	Vi = –8 V, V_{DS} = 0
	I_{IH2}	—	—	–50	μA	Vi = –3.5 V, V_{DS} = 0
	I_{IL}	—	—	–1	μA	Vi = –1.2 V, V_{DS} = 0
Input current (gate shut down)	$I_{IH(sd)1}$	—	–0.8	—	mA	Vi = –8 V, V_{DS} = 0
	$I_{IH(sd)2}$	—	–0.35	—	mA	Vi = –3.5 V, V_{DS} = 0
Shut down temperature	Tsd	—	175	—	°C	Channel temperature (dv/dt V_{GS} ≥ 500 V/ms)
Gate operation voltage	Vop	–3.5	—	–12	V	
Drain current (Current limitation value)	$I_{D\ limt}$	–10	—	—	A	V_{GS} = –12 V, V_{DS} = –10 V Notes 4

Notes: 4. Pulse test

Electrical Characteristics

(Ta = 25°C)

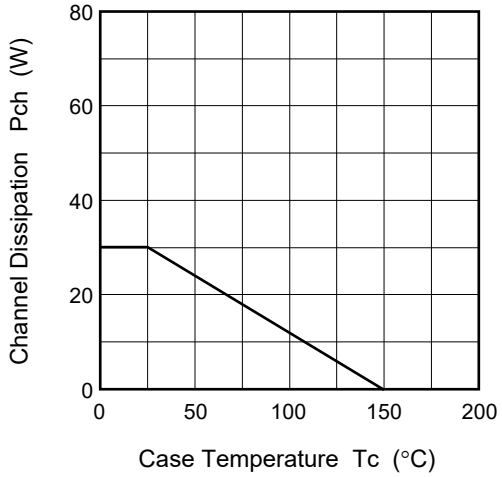
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain current	I_{D1}	—	—	–4	A	V_{GS} = –3.5 V, V_{DS} = –10 V
	I_{D2}	—	—	–10	mA	V_{GS} = –1.2 V, V_{DS} = –10 V
	I_{D3}	–10	—	—	A	V_{GS} = –12 V, V_{DS} = –10 V Notes 5
Drain to source breakdown voltage	$V_{(BR)DSS}$	–60	—	—	V	I_D = –10 mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	–16	—	—	V	I_G = –800 μA, V_{DS} = 0
	$V_{(BR)GSS}$	2.5	—	—	V	I_G = 100 μA, V_{DS} = 0
Gate to source leak current	I_{GSS1}	—	—	–100	μA	V_{GS} = –8 V, V_{DS} = 0
	I_{GSS2}	—	—	–50	μA	V_{GS} = –3.5 V, V_{DS} = 0
	I_{GSS3}	—	—	–1	μA	V_{GS} = –1.2 V, V_{DS} = 0
	I_{GSS4}	—	—	100	μA	V_{GS} = 2.4 V, V_{DS} = 0
Input current (shut down)	$I_{GS(OP)1}$	—	–0.8	—	mA	V_{GS} = –8 V, V_{DS} = 0
	$I_{GS(OP)2}$	—	–0.35	—	mA	V_{GS} = –3.5 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	–10	μA	V_{DS} = –60 V, V_{GS} = 0
Gate to source cutoff current	$V_{GS(off)}$	–2.2	—	–3.4	V	V_{DS} = –10 V, I_D = –1 mA
Forward admittance	$\|y_{fs}\|$	4	8	—	S	I_D = –5 A, V_{DS} = –10 V Notes 5
Static drain to source on state resistance	$R_{DS(on)}$	—	75	110	mΩ	I_D = –5 A, V_{GS} = –6 V Notes 5
	$R_{DS(on)}$	—	58	75	mΩ	I_D = –5 A, V_{GS} = –10 V Notes 5
Output capacitance	Coss	—	355	—	pF	V_{DS} = –10 V, V_{GS} = 0, f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	4.5	—	μs	V_{GS} = –10 V, I_D= –5 A, R_L = 6 Ω
Rise time	t_r	—	4.0	—	μs	
Turn-off delay time	$t_{d(off)}$	—	1.8	—	μs	
Fall time	t_f	—	1.3	—	μs	
Body-drain diode forward voltage	V_{DF}	—	0.87	—	V	I_F = –10 A, V_{GS} = 0
Body-drain diode reverse recovery time	t_{rr}	—	209	—	ns	I_F = –10 A, V_{GS} = 0 di_F/dt = 50 A/μs
Over load shut down operation time Note 6	t_{os1}	—	2.3	—	ms	V_{GS} = –6 V, V_{DD} = –16 V

Notes: 5. Pulse test

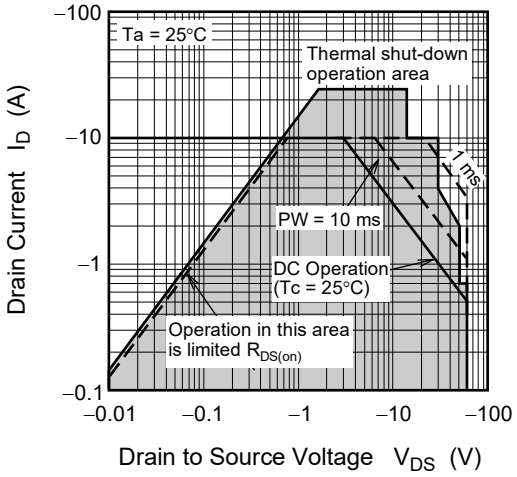
6. Including the junction temperature rise of the over loaded condition

Main Characteristics

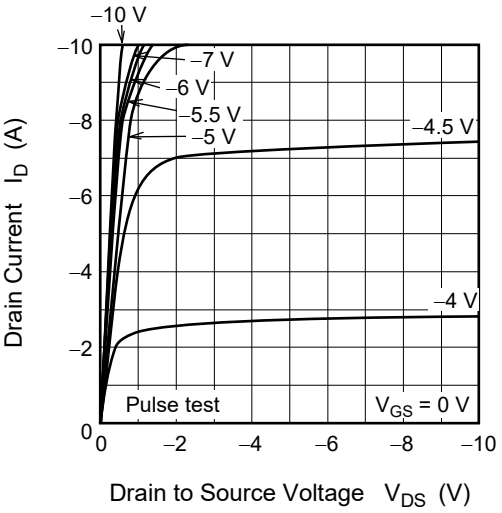
Power vs. Temperature Derating



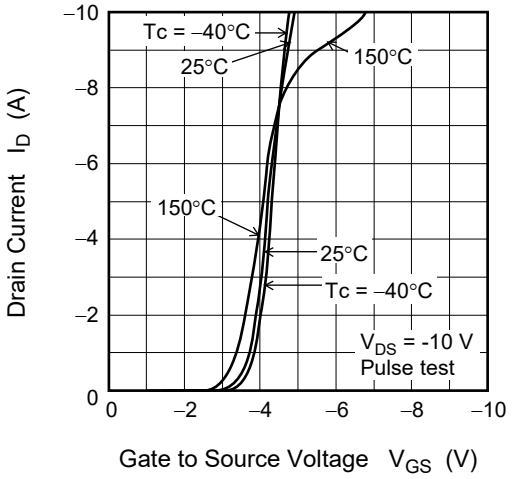
Maximum Operation Safe Area



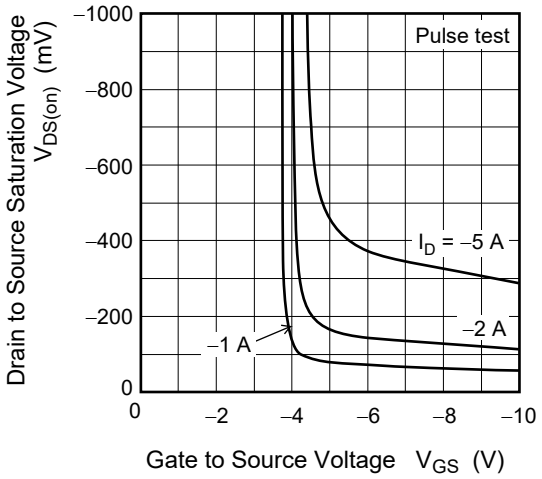
Typical Output Characteristics



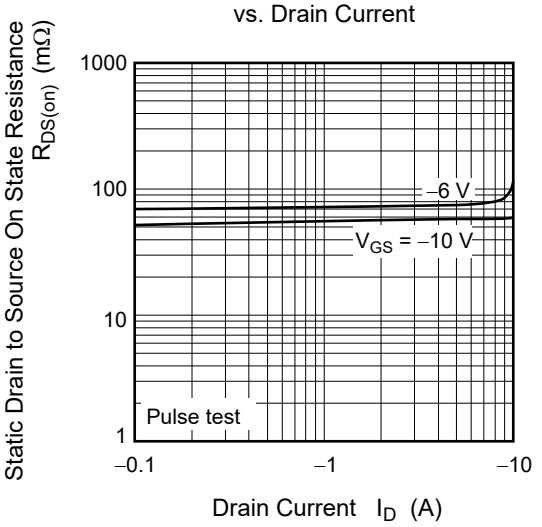
Typical Transfer Characteristics



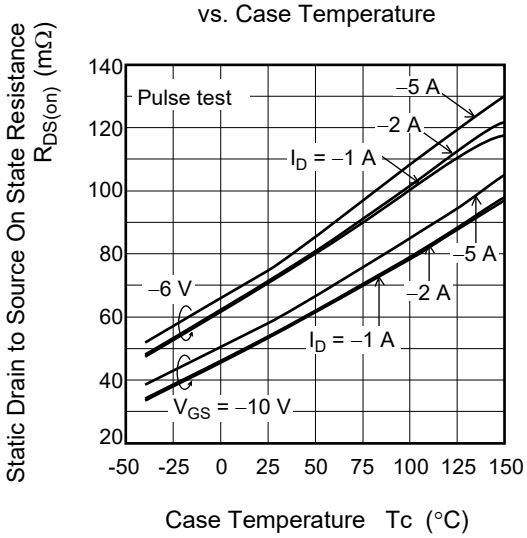
Drain to Source Saturation Voltage vs. Gate to Source Voltage



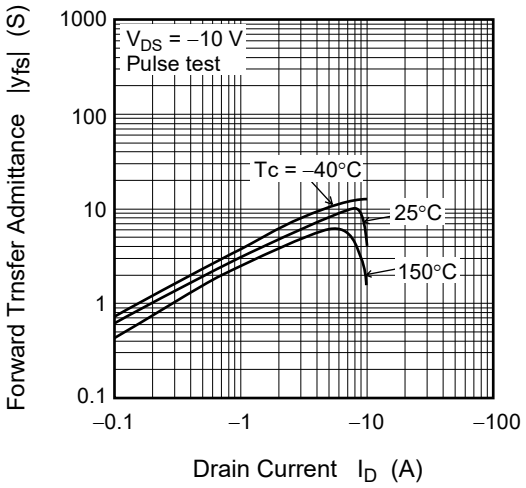
Static Drain to Source On State Resistance vs. Drain Current



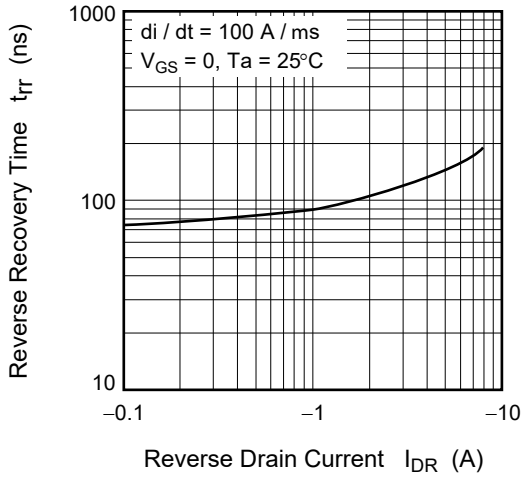
Static Drain to Source On State Resistance vs. Case Temperature



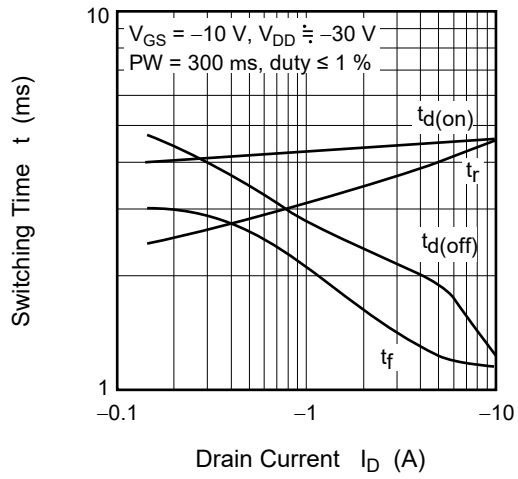
Forward Transfer Admittance vs. Drain Current



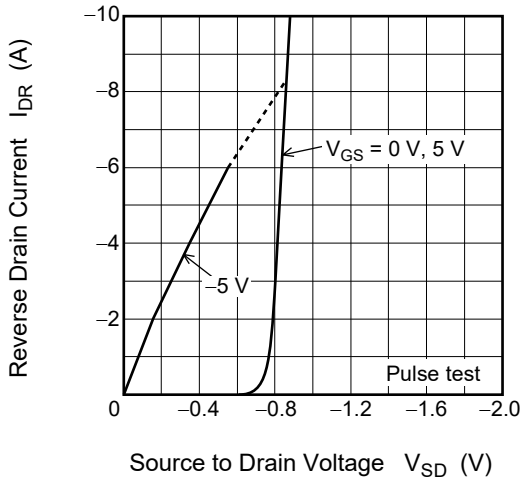
Body-Drain Diode Reverse Recovery Time



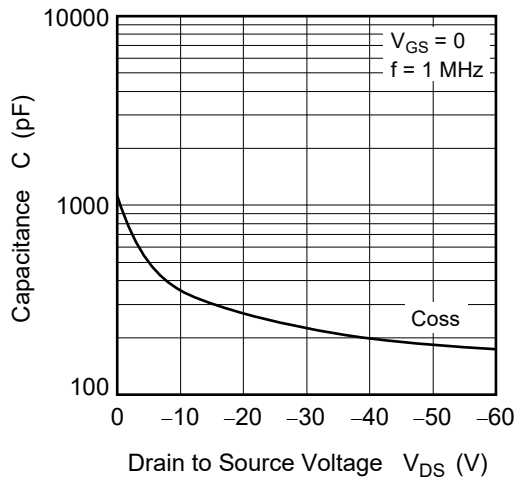
Switching Characteristics



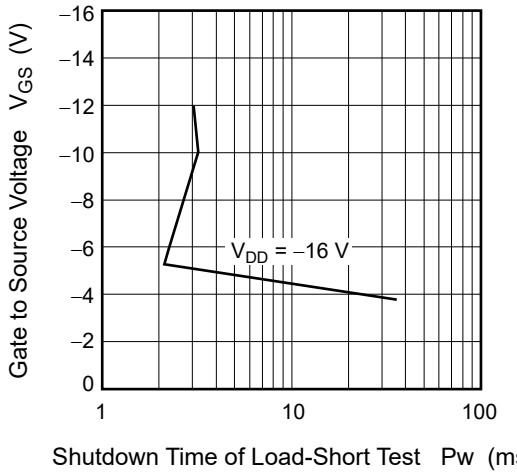
Reverse Drain Current vs. Source to Drain Voltage



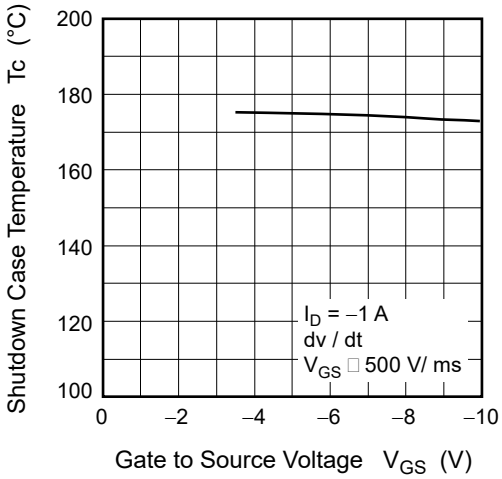
Typical Capacitance vs. Drain to Source Voltage



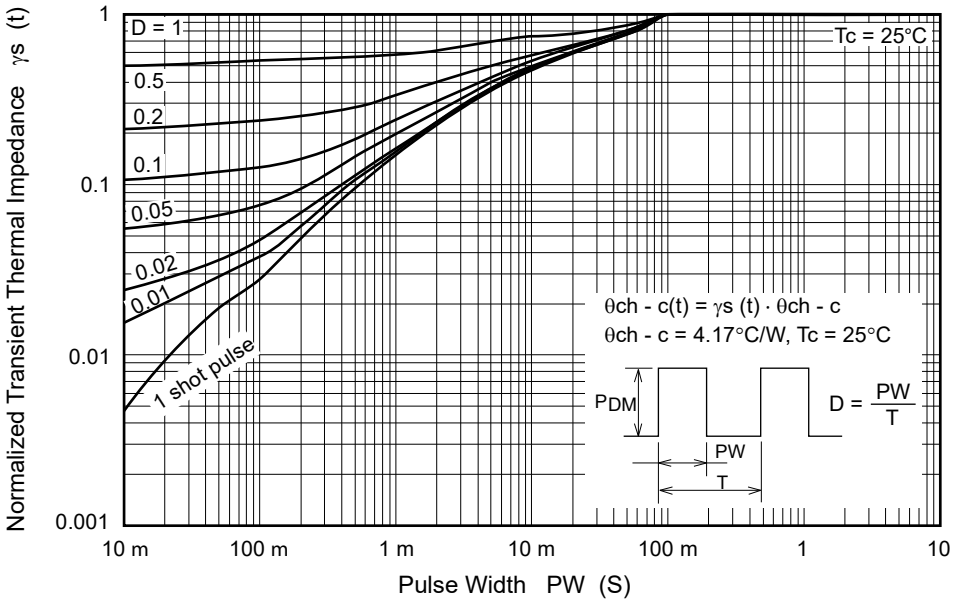
Gate to Source Voltage vs.
Shutdown Time of Load-Short Test



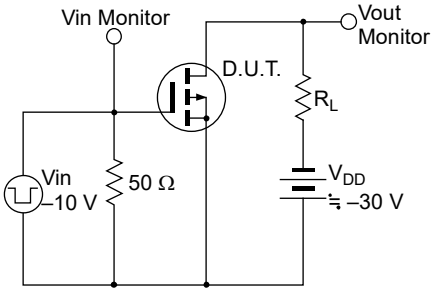
Shutdown Case Temperature vs.
Gate to Source Voltage



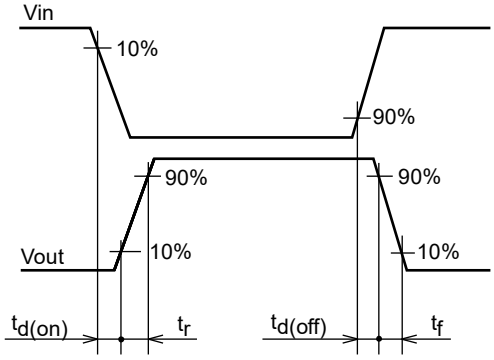
Normalized Transient Thermal Impedance vs. Pulse Width



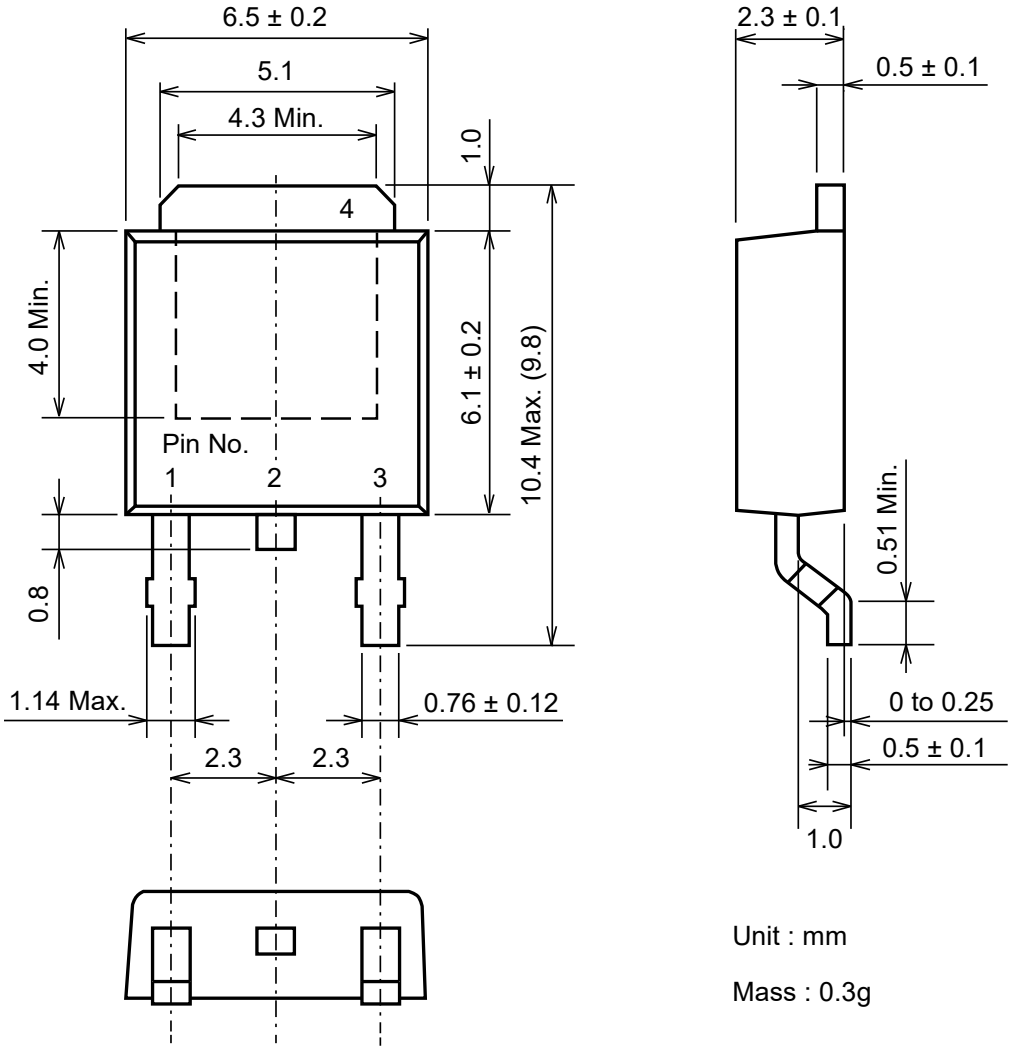
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Part No.	Quantity	Shipping container
RJE0605JPV-00-Q7	2500 pcs/reel	Taping

Note: The symbol of 2nd "-" is occasionally presented as "#".

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